

HIGH CURRENT APPLICATION.

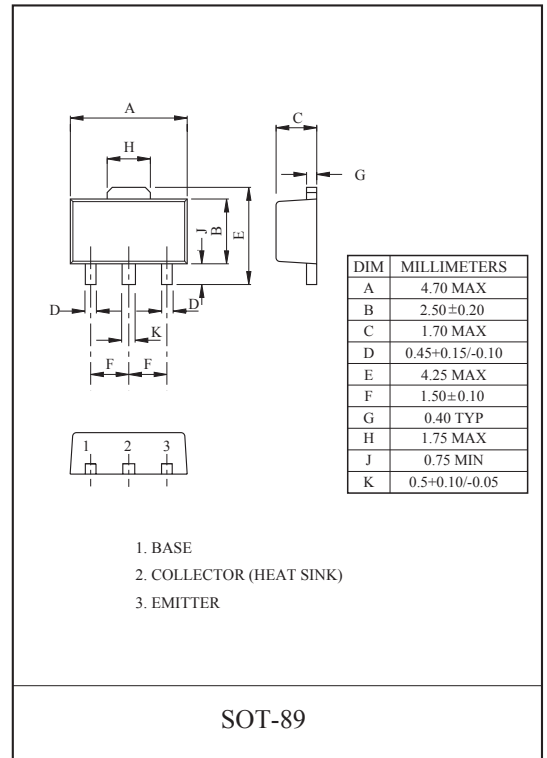
### FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTC4375.

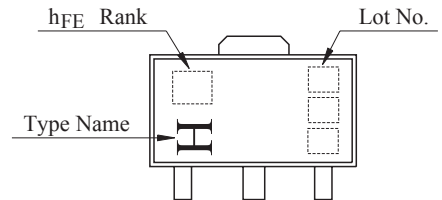
### MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CB0}$	-30	V
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-1.5	A
Base Current	$I_B$	-0.3	A
Collector Power Dissipation	$P_C$	500	mW
	$P_C^*$	1	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55 ~ 150	°C

$P_C^*$  : KTA1663 mounted on ceramic substrate (250mm<sup>2</sup>x0.8t)



### Marking



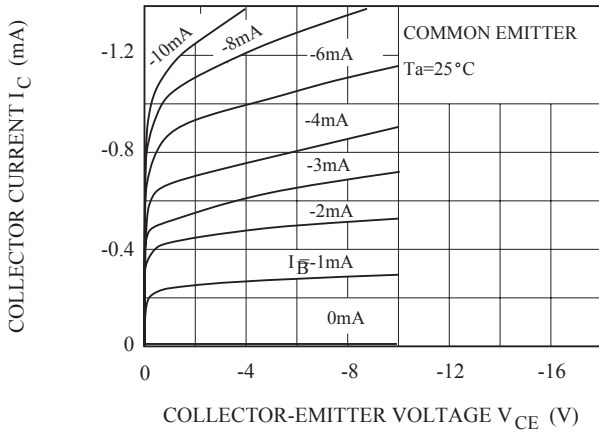
### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CB0}$	$V_{CB}=-30V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5.0	-	-	V
DC Current Gain	$h_{FE}$ (Note)	$V_{CE}=-2V, I_C=-500mA$	100	-	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-0.03A$	-	-	-2.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=-2V, I_C=-500mA$	-	-	-1.0	V
Transition Frequency	$f_T$	$V_{CE}=-2V, I_C=-500mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$	-	-	50	pF

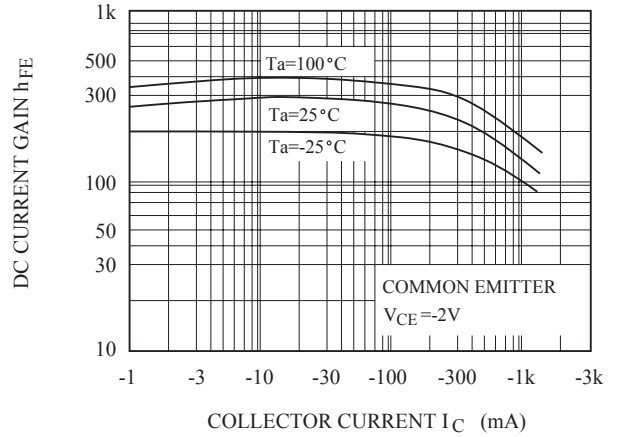
Note :  $h_{FE}$  Classification    O:100 ~ 200,    Y:160 ~ 320

# KTA1663

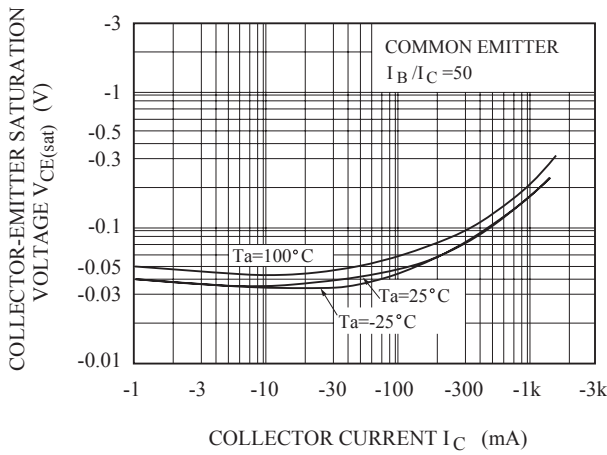
$I_C - V_{CE}$



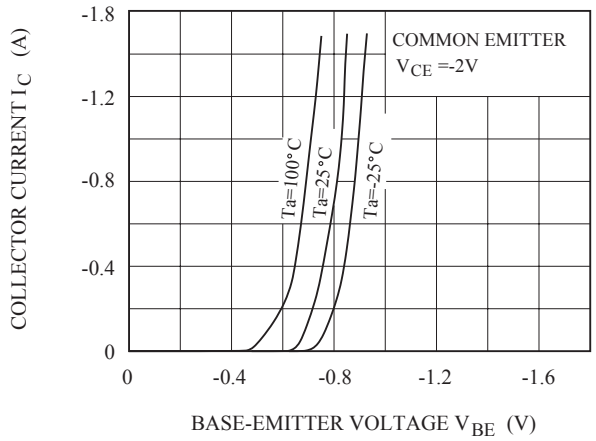
$h_{FE} - I_C$



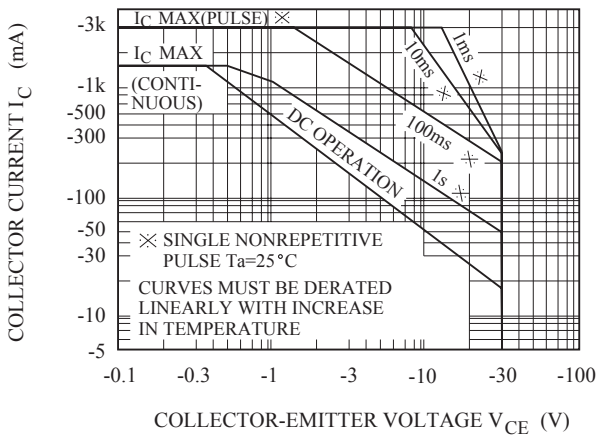
$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



SAFE OPERATING AREA



$P_c - T_a$

